

# **BUK9K17-60E**

# Dual N-channel 60 V, 17 m $\Omega$ logic level MOSFET

Product data sheet

# 1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol                                | Parameter                            | Conditions   |     | Min | Тур | Max | Unit |
|---------------------------------------|--------------------------------------|--|-----|-----|-----|-----|------|
| V <sub>DS</sub>                       | drain-source voltage                 | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  |     | -   | -   | 60  | V    |
| I <sub>D</sub>                        | drain current                        | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>  | [1] | -   | -   | 26  | Α    |
| P <sub>tot</sub>                      | total power dissipation              | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>   |     | -   | -   | 53  | W    |
| Static characte                       | Static characteristics FET1 and FET2 |  |     |     |     |     |      |
| R <sub>DSon</sub>                     | drain-source on-state resistance     | $V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$   |     | -   | 14  | 17  | mΩ   |
| Dynamic characteristics FET1 and FET2 |                                      |  |     |     |     |     |      |
| $Q_{GD}$                              | gate-drain charge                    | I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;<br>T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> |     | -   | 5.7 | -   | nC   |

[1] Continuous current is limited by package.



Dual N-channel 60 V, 17  $m\Omega$  logic level MOSFET

# **Pinning information**

Table 2. **Pinning information** 

| Pin | Symbol | Description | Simplified outline            | Graphic symbol |
|-----|--------|-------------|-------------------------------|----------------|
| 1   | S1     | source1     | 8 7 6 5                       | D1 D1 D2 D2    |
| 2   | G1     | gate1       | 1/                            |                |
| 3   | S2     | source2     |                               |                |
| 4   | G2     | gate2       |                               |                |
| 5   | D2     | drain2      |                               |                |
| 6   | D2     | drain2      | l î î î                       | mbk725         |
| 7   | D1     | drain1      | 1 2 3 4<br>LFPAK56D (SOT1205) |                |
| 8   | D1     | drain1      | 2                             |                |

# **Ordering information**

Table 3. **Ordering information** 

| Type number | Package  |  |         |  |  |
|-------------|----------|--|---------|--|--|
|             | Name     | Description  | Version |  |  |
| BUK9K17-60E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |  |  |

#### **Marking** 7.

Marking codes Table 4.

| Type number | Marking code |
|-------------|--------------|
| BUK9K17-60E | 91760E       |

#### **Limiting values** 8.

**Limiting values** Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |        | Min     | Max              | Unit              |
|------------------|-------------------------|---|--------|---------|------------------|-------------------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C                     |        | -       | 60               | V                 |
| $V_{DGR}$        | drain-gate voltage      | $R_{GS}$ = 20 k $\Omega$  |        | -       | 60               | V                 |
| $V_{GS}$         | gate-source voltage     | T <sub>j</sub> ≤ 175 °C; DC   |        | -10     | 10               | V                 |
|                  |                         | T <sub>j</sub> ≤ 175 °C; Pulsed                                     | [1][2] | -15     | 15               | V                 |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                              |        | -       | 53               | W                 |
| I <sub>D</sub>   | drain current           | $T_{mb} = 25  ^{\circ}\text{C}; V_{GS} = 5  \text{V}; Fig. 2$       | [3]    | -       | 26               | Α                 |
|                  |                         | T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>      |        | -       | 26               | Α                 |
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| Symbol               | Parameter                                    | Conditions  |        | Min | Max | Unit |
|----------------------|--|---|--------|-----|-----|------|
| I <sub>DM</sub>      | peak drain current                           | $T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3                                     |        | -   | 148 | Α    |
| T <sub>stg</sub>     | storage temperature                          |   |        | -55 | 175 | °C   |
| Tj                   | junction temperature                         |   |        | -55 | 175 | °C   |
| Source-dra           | in diode FET1 and FET2                       |   | ·      | 1   |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C   | [3]    | -   | 26  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$                                  |        | -   | 148 | Α    |
| Avalanche            | Ruggedness FET1 and FET2                     |   |        |     |     | ,    |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $I_D$ = 26 A; $V_{sup} \le 60 \text{ V}$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 4 | [4][5] | -   | 64  | mJ   |

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering  $T_i$  and or  $V_{GS}$ .
- [3] Continuous current is limited by package.
- [4] Refer to application note AN10273 for further information
- 5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

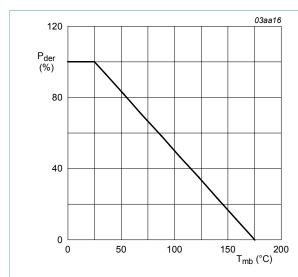


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

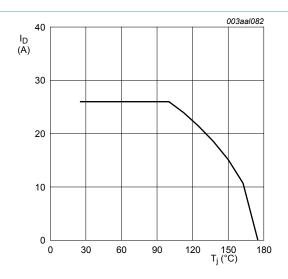


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{\rm GS} \geq 5V$$

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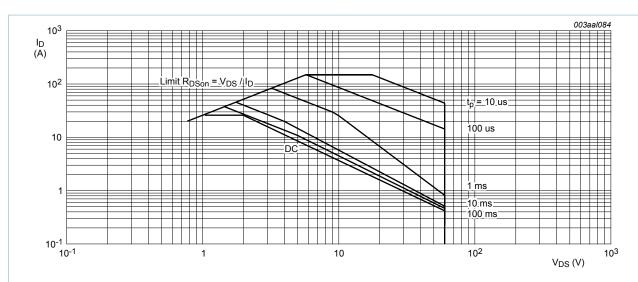
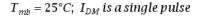


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



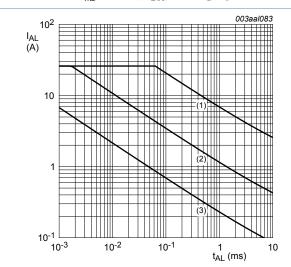


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j \text{ (init)}} = 25^{\circ}C$ ; (2)  $T_{j \text{ (init)}} = 150^{\circ}C$ ; (3) Repetitive Avalanche

### 9. Thermal characteristics

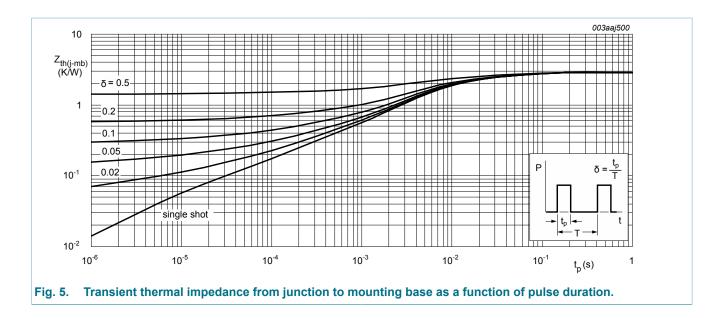
Table 6. Thermal characteristics

| Symbol                | Parameter   | Conditions  | Min | Тур | Max  | Unit |
|-----------------------|---|---|-----|-----|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5  | -   | -   | 2.84 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |

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## 10. Characteristics

Table 7. Characteristics

| Symbol  | Parameter                                    | Conditions   | Min | Тур  | Max  | Unit |
|---|--|--|-----|------|------|------|
| Static chara  | acteristics FET1 and FET2                    |  | ,   | '    |      |      |
| V <sub>(BR)DSS</sub> drain-source breakdown voltage |  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                | 54  | -    | -    | V    |
|   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 60   | -   | -    | V    |      |
| V <sub>GS(th)</sub>                                 | gate-source threshold voltage                | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$<br>Fig. 9; Fig. 10                         | 1.4 | 1.7  | 2.1  | V    |
|   |  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C;<br>Fig. 9; Fig. 10 | 0.5 | -    | -    | V    |
|   |  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C;<br>Fig. 9; Fig. 10                                 | -   | -    | 2.45 | V    |
| I <sub>DSS</sub> drain leakage                      | drain leakage current                        | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                  | -   | 0.02 | 1    | μA   |
|   |  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                                 | -   | -    | 500  | μA   |
| I <sub>GSS</sub>                                    | gate leakage current                         | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                 | -   | 2    | 100  | nA   |
|   |  | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>                                   | drain-source on-state                        | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>                   | -   | 14   | 17   | mΩ   |
|   | resistance                                   | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C;<br>Fig. 11; Fig. 12             | -   | 31.6 | 38.4 | mΩ   |
|   |  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C;<br>Fig. 11                      | -   | 12.4 | 15.6 | mΩ   |
| Dynamic ch  | naracteristics FET1 and FE                   | ET2  | '   |      |      |      |
| Q <sub>G(tot)</sub>                                 | total gate charge                            | I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;                                  | -   | 16.5 | -    | nC   |
| Q <sub>GS</sub>                                     | gate-source charge                           | T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>  | -   | 3.3  | -    | nC   |

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| Symbol             | Parameter                    | Conditions   | Min | Тур  | Max  | Unit |
|--------------------|------------------------------|--|-----|------|------|------|
| $Q_{GD}$           | gate-drain charge            |  | -   | 5.7  | -    | nC   |
| C <sub>iss</sub>   | input capacitance            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;  | -   | 1667 | 2223 | pF   |
| C <sub>oss</sub>   | output capacitance           | T <sub>j</sub> = 25 °C; <u>Fig. 15</u>   | -   | 160  | 193  | pF   |
| C <sub>rss</sub>   | reverse transfer capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 48 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}; Fig. 15$                                | -   | 91   | 124  | pF   |
| t <sub>d(on)</sub> | turn-on delay time           | $V_{DS} = 48 \text{ V}; R_L = 5 \Omega; V_{GS} = 5 \text{ V};$<br>$R_{G(ext)} = 5 \Omega; T_j = 25 \text{ °C}; I_D = 10 \text{ A}$ | -   | 10.7 | -    | ns   |
| t <sub>r</sub>     | rise time                    |  | -   | 20   | -    | ns   |
| $t_{d(off)}$       | turn-off delay time          |  | -   | 23   | -    | ns   |
| t <sub>f</sub>     | fall time                    |  | -   | 19.2 | -    | ns   |
| Source-dra         | in diode FET1 and FET2       |  |     |      | '    |      |
| $V_{SD}$           | source-drain voltage         | $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$   | -   | 0.78 | 1.2  | V    |
| t <sub>rr</sub>    | reverse recovery time        | $I_S = 10 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;   | -   | 20.3 | -    | ns   |
| Q <sub>r</sub>     | recovered charge             | V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C   | -   | 16.7 | -    | nC   |

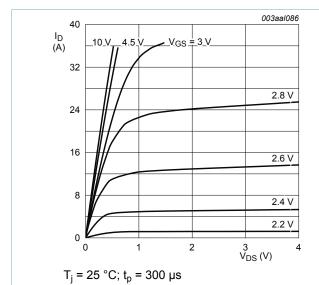


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

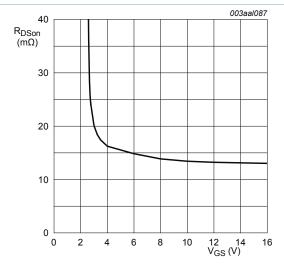


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

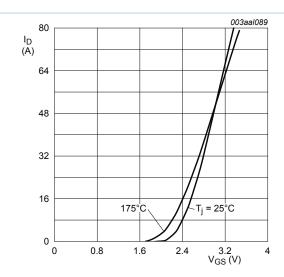


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



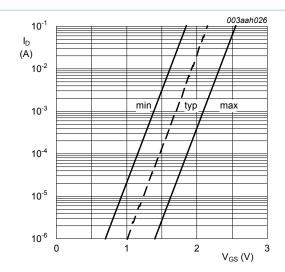


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

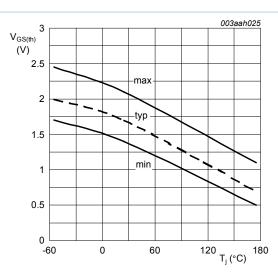
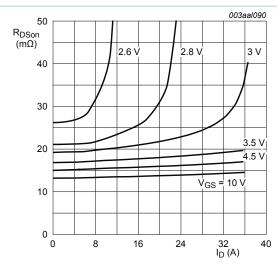


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA;  $V_{DS} = V_{GS}$ 



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

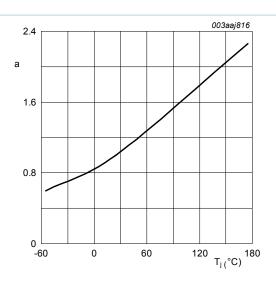


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

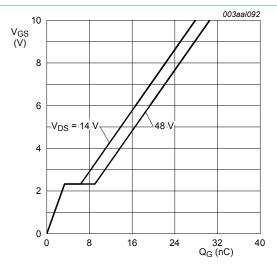


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C;  $I_D = 10A$ 

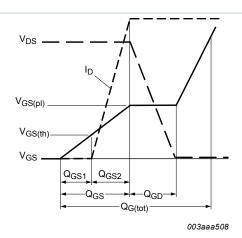


Fig. 13. Gate charge waveform definitions

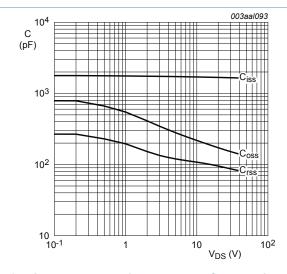


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

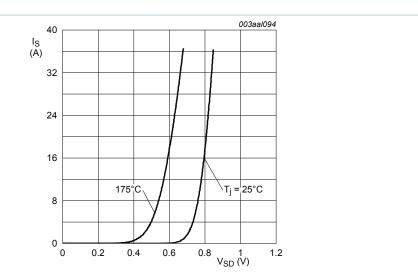


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

#### Dual N-channel 60 V, 17 $m\Omega$ logic level MOSFET

## 11. Package outline

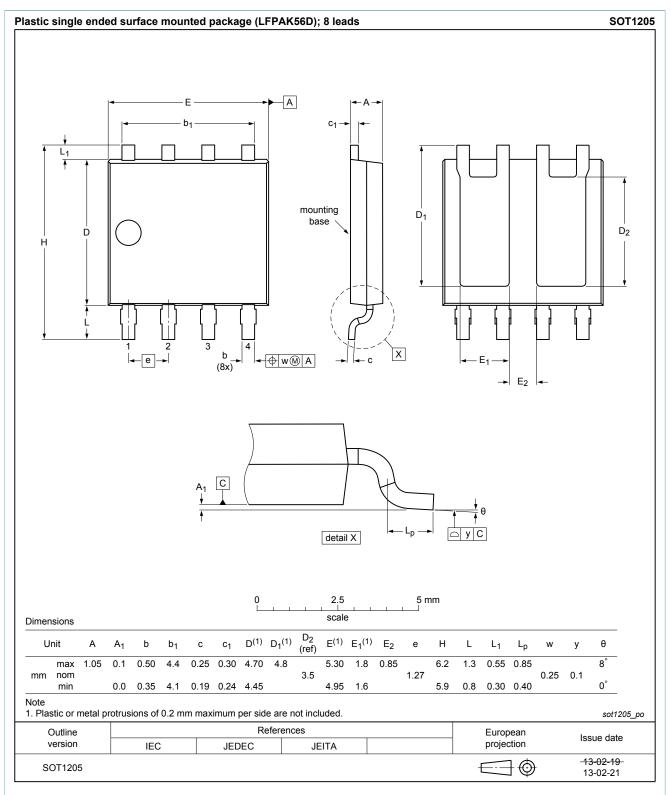


Fig. 17. Package outline LFPAK56D (SOT1205)

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|--------------------------------------|--------------------|---|
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## Dual N-channel 60 V, 17 $m\Omega$ logic level MOSFET

## 13. Contents

| 1    | General description     | 1  |
|------|-------------------------|----|
| 2    | Features and benefits   | 1  |
| 3    | Applications            | 1  |
| 4    | Quick reference data    | 1  |
| 5    | Pinning information     | 2  |
| 6    | Ordering information    | 2  |
| 7    | Marking                 | 2  |
| 8    | Limiting values         | 2  |
| 9    | Thermal characteristics | 4  |
| 10   | Characteristics         | 5  |
| 11   | Package outline         | 10 |
| 12   | Legal information       | 11 |
| 12.1 | Data sheet status       | 11 |
| 12.2 | Definitions             | 11 |
| 12.3 | Disclaimers             | 11 |
| 12.4 | Trademarks              | 12 |

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Date of release: 19 March 2014

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